

## 2SA683 / 2SA684 PNP Silicon Epitaxial Planar Transistor

for low frequency power amplification and driver amplification

The transistor is subdivided into three group, Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package  
Weight approx. 0.19g

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	30	V
2SA683		50	
Collector Emitter Voltage	$-V_{CEO}$	25	V
2SA684		40	
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	1	A
Peak Collector Current	$-I_P$	1.5	A
Power Dissipation	$P_{tot}$	1	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_S$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_{amb} = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 10\text{ V}$ , $-I_C = 500\text{ mA}$  at $-V_{CE} = 5\text{ V}$ , $-I_C = 1\text{ A}$	Current Gain Group Q R S $h_{FE}$	85	-	170	-
		120	-	240	-
		170	-	340	-
		50	-	-	-
Collector Cutoff Current at $-V_{CB} = 20\text{ V}$	$-I_{CBO}$	-	-	0.1	$\mu\text{A}$
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	30	-	-	V
2SA684		50	-	-	
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	25	-	-	V
2SA684		40	-	-	
Emitter Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$ , $-I_B = 50\text{ mA}$	$-V_{CEsat}$	-	-	0.4	V
Base Emitter Saturation Voltage at $-I_C = 500\text{ mA}$ , $-I_B = 50\text{ mA}$	$-V_{BEsat}$	-	-	1.2	V
Transition Frequency at $-V_{CB} = 10\text{ V}$ , $I_E = 50\text{ mA}$ , $f = 200\text{ MHz}$	$f_T$	-	200	-	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$	$C_{ob}$	-	-	30	pF



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